

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-13. (Canceled)

14. (Currently Amended) Method for delineating a conducting element disposed on an insulating layer, ~~comprising the method comprising:~~

depositing ~~deposition of~~ a conducting layer on the front face of the insulating layer disposed on a substrate,

forming ~~formation of~~ a mask on at least one area of the conducting layer designed to form the conducting element, so as to delineate in the conducting layer at least one complementary area not covered by the mask,

introducing oxygen to the complementary areas of the conducting layer ~~layer,~~ and being rendered insulating by oxidation, ~~method comprising formation~~

oxidizing in said the complementary areas of the conducting layer, ~~of to form~~ a volatile oxide from the material of the conducting layer and ~~the oxygen arising from~~ oxidation, wherein the complementary areas of the conducting layer are rendered insulating by oxidation-evaporating and evaporate at least partly.

15. (Currently Amended) Method according to claim 14, wherein ~~oxidation~~ oxidizing the complementary areas of the conducting layer is performed before the mask is removed.

16. (Currently Amended) Method according to claim 14, wherein ~~oxidation~~ oxidizing the complementary areas of the conducting layer is performed after the mask has been removed.

17. (Currently Amended) Method according to claim 14, wherein formation of the volatile oxide and evaporation of the conducting layer take place during ~~oxidation~~ the oxidizing of the complementary areas of the conducting layer.

18. (Currently Amended) Method according to claim 14, wherein oxidizing the complementary areas of the conducting layer comprises ~~the volatile oxide is formed, after oxidation,~~ by stabilizing and evaporating annealing.

19. (Currently Amended) Method according to claim 14, wherein ~~oxidation of~~ introducing oxygen to the complementary areas of the conducting layer comprises oxygen implantation.

20. (Currently Amended) Method according to claim 14, wherein ~~oxidation of~~ oxidizing the complementary areas of the conducting layer comprises thermal oxidation.

21. (Currently Amended) Method according to claim 14, wherein the complementary areas of the conductive layer rendered insulating by oxidation have a thickness at least equal to one atomic layer.

22. (Currently Amended) Method according to claim 14 wherein ~~deposition the~~ conducting layer depositing step of the conducting layer comprises at least:

a first depositing step of deposition of to form a first conducting layer and

a second depositing step of deposition of to form a second conducting layer on the front face of the first conducting layer.

23. (Currently Amended) Method for delineating a conducting element disposed on an insulating layer, comprising:

deposition of a conducting layer on the front face of the insulating layer disposed on a substrate,

formation of a mask on at least one area of the conducting layer designed to form the conducting element, so as to delineate in the conducting layer at least one

complementary area not covered by the mask, the complementary areas of the conducting layer being rendered insulating by oxidation, method comprising formation, in said complementary areas of the conducting layer, of a volatile oxide from the material of the conducting layer and the oxygen arising from oxidation, the conducting layer evaporating at least partly,

wherein the deposition of the conducting layer comprises a first step of deposition of a first conducting layer and a second step of deposition of a second conducting layer on the front face of the first conducting layer, and

etching of the second conducting layer after formation of the mask and before oxidation. ~~Method according to claim 22, comprising etching of the second conducting layer after formation of the mask and before oxidation.~~

24. (Currently Amended) Method according to ~~claim 22~~ claim 23, wherein the material of the first conducting layer is taken from the group comprising tungsten, molybdenum, nickel and cobalt, and the material of the second conducting layer is polycrystalline silicon.

25-26. (Canceled)